Quantum threshold reflection of He atom beams from rough surfaces

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Abstract

Quantum reflection of thermal He atoms from various surfaces (glass slide, GaAs wafer, flat and structured Cr) at grazing conditions is studied within the elastic close-coupling formalism. Comparison with the experimental results of B.S. Zhao et al, Phys. Rev. Lett. 105, 133203 (2010) is quite reasonable but the conclusions of the present theoretical analysis are different from those discussed in the experimental work. The universal linear behavior observed in the dependence of the reflection probability on the incident wave vector component perpendicular to the surface is only valid at small values of the component whereas, at larger values, deviation from the linearity is evident, approaching a quadratic dependence at higher values. The surface roughness seems to play no important role in this scattering. Moreover, the claim that one observes a transition from quantum to classical reflection seems to be imprecise.
I. INTRODUCTION

Matter wave diffraction and interferometry are very interesting topics because, unlike optical effects observed by photons, these studies lead to a better knowledge of the interaction between particles and surfaces. This interaction is usually divided into two regions, short and long range distances. The short distances are dominated by the Pauli and Coulomb repulsion between electrons of the incoming particle and the surface and the long distances are governed mainly by the van der Waals-Casimir attraction. We talk about classical reflection when particles reach the inner region (turning points) corresponding to the repulsive part of the interaction potential. On the other hand, when the reflection comes from the long range attractive part, one talks about quantum threshold reflection. Lennard-Jones and Devonshire\textsuperscript{1} first recognized this behavior in atom-surface scattering and Kohn\textsuperscript{2} showed later on that quantum reflection leads to a zero sticking probability at threshold. He pointed out that this reflection is a quantum interference process between the incoming and reflected waves. Senn\textsuperscript{3} showed that, for general one-dimensional forces which vanish as the coordinate goes to ±∞, the reflection probability goes to unity at threshold except when the potential supports a zero energy resonance state. The reflection coefficient decreases from unity according to $|R| \sim 1 - 2kb + 2k^2b^2 \sim \exp(-2kb)$, where $k$ is the incident wave vector and $b$ a characteristic length which depends on the specifics of the particle surface interaction. This universal behavior is a direct result of boundary conditions and continuity of the wave function and its derivative. When considering scattering from surfaces which occurs in three dimensional space, $k$ should be replaced by its component red perpendicular to the surface.

This quantum threshold reflection phenomenon has been observed for the scattering of ultra cold metastable He atoms on silicon\textsuperscript{4} and for rare-gas atoms and small clusters on gratings and surfaces\textsuperscript{5-8} and on a periodic array of half planes\textsuperscript{9}. At threshold conditions, where the incident energy is very small, the maximum of the scattered wavefunction is located far away from the grating/surface due to the very long de Broglie wave length of the incident particle. This led mistakenly to the idea that quantum reflection takes place far away from the grating/surface, at distances of typically tens or hundreds of nanometers. Quantum threshold reflection was claimed to be governed by the long-range attractive van der Waals-Casimir potential tail which falls off faster than $r^{-2}$\textsuperscript{10,11}. It was claimed that the fact that the very weakly bound He$_2$ molecule which is reflected without dissociating is...
further proof that only the long range weak forces are at play and these are too weak to
dissociate even such a fragile bond. This would not be the case if the dimer reaches the
classical turning point of the interaction potential.

In the semiclassical framework, and within the $k$ linear dependence regime, the semiclas-
sical description of the scattering dynamics breaks down. Far away from the grating/surface,
the long range attractive potential exhibits a region in which the local de Broglie wavelength
is not slowly varying, invalidating a semiclassical description. This occurs in the so called
"badlands" region of the interaction potential. Quantum reflection was thus associated with
this badlands region through a function called "quantality" whose absolute value displays
large deviations from unity in a confined region of the potential, implying that in this region
quantum effects are important. In a series of papers, we have recently demonstrated
teoretically and numerically that quantum threshold reflection is determined by the
whole range of the interaction potential. We have observed that the short range region is
also critical for obtaining theoretical reflection probabilities and diffraction patterns which
are in fairly good agreement with the experimental results of Refs. These calculations
were carried out by using the elastic close-coupling (CC) formalism, which is numerically
exact when convergence is reached. To distinguish between quantum and classical reflec-
tion in this type of theoretical calculations, complex absorbing boundary conditions which
prevent the classical reflection from occurring have been employed. In Ref. we have
also shown that the badlands region of the interaction potential is irrelevant in quantum
threshold reflection since the wavelength of the scattering particles at threshold is much
longer than the rather small spatial extent of this region.

In the work presented in this paper, we have extended our previous studies to analyze
and discuss previously reported coherent reflection of He atom beams from rough surfaces
at grazing incidence. When the component of the incident wave vector of the incoming
atom perpendicular to the surface is very small, experimental and theoretical reflection
probabilities seem to be only dependent on this normal component and approach unity
when it vanishes confirming the corresponding universal behavior. Deviations from linearity
are found only at larger values of this normal component. Moreover, we do not find a
transition from quantum to classical reflection when increasing the normal component of
the wave vector, as previously reported in Ref. Finally, the surface roughness at threshold
conditions and grazing angles appears to play no important role in this scattering.
In Section II we review some of the experimental considerations. The elastic CC formalism is only briefly described in Section III since it has already been extensively reported on elsewhere. Theoretical results are presented and compared with the experimental ones in Section IV, this is followed by a discussion justifying our different interpretations and conclusions.

II. EXPERIMENTAL CONSIDERATIONS

The experiments we want to analyze have been described in detail in Refs. Experimental results have been obtained from a supersonic beam expansion of He atoms at different stagnation temperatures $T_0 = 300, 50, \text{and } 8.7 \text{ K}$ corresponding to incidence wave vectors $k$ of $112, 46 \text{ and } 18 \text{ nm}^{-1}$, respectively. In order to maintain a high atomic flux and narrow velocity distribution of the incident beam and avoid cluster formation, different stagnation pressures $P_0 = 31, 26 \text{ and } 0.5 \text{ bar}$ have been used. In the cryogenic free jet expansion of incident particles, the incident kinetic energy is given by $E_i = \frac{5}{2} k_B T_0$ ($k_B$ is Boltzmann’s constant). Four types of surfaces have been considered in these experiments: (i) a glass slide which is a simple standard microscope slide (ISO Norm 8037/I), 1 mm thick and with a surface area of 76 x 26 mm$^2$; (ii) the commercial GaAs wafer which is cut along the (100) direction and is 50 mm in diameter; (iii) a flat chromium surface of 100 x 30 mm$^2$ area used for comparison with the grating surface (iv) a 20-µm-period chromium grating previously used in Ref. (a 56-mm-long microstructured array of 110-nm-thick, 10 µm-wide and 5-mm-long parallel chromium strips on a flat quartz substrate). Surfaces are expected to be oxidized or oxygen covered but in spite of this contamination, at grazing angles intense specular reflection peaks are still observable. Since no information about the roughness of the surfaces employed in the experiments is provided, they are going to be assumed flat (except for type (iv)) and well described by one dimension in the $x$-direction. The incident angle $\theta_i$ is usually varied below 0.1 mrad and up to 25 mrad and measured with respect to the surface plane.

Angular distributions or diffraction patterns of in-saggital-plane ($x,z$-plane) scattering are recorded by rotating the detector and measuring the He signal at each angle. The diffraction angles $\theta_n$ are given by the conservation of the momentum or Bragg’s law

$$\cos \theta_i - \cos \theta_n = \frac{n \lambda}{d} = \frac{2\pi n}{d k}$$ (1)
where \( \lambda \) is the de Broglie wave length of the incident particle and the diffraction order is given by \( n \). Negative diffraction orders correspond to diffraction angles close to the surface grating, that is, energy in the perpendicular direction is transferred to the parallel direction. The reflection or diffraction probabilities are obtained from the integrated intensity of the reflected peak normalized to the peak area of the incident beam and the total reflection probability is the sum of all of them. Final results are plotted as a function of the corresponding perpendicular wave vector, that is, along the \( z \)-direction

\[
k_{\text{perp}} \approx \sqrt{\frac{5mk_B T_0}{\hbar}} \sin \theta_i
\]

with \( m \) being the He atomic mass.

The main conclusions of the authors of this experimental work are that at low \( k_{\text{perp}} \) values the reflection probability is dominated by quantum threshold reflection, which is manifested by a steep linear decrease of the reflection probability with increasing \( k_{\text{perp}} \). At larger \( k_{\text{perp}} \), the corresponding results start to fan out and are rationalized in terms of classical reflection from the inner region of the repulsive interaction potential. The dividing line between both regimes is claimed to be around \( k_{\text{perp}} = 0.3 \, nm^{-1} \) and independent of the type of surface studied. Only the fanning out effect is explained in terms of the surface roughness.

III. THEORY

The theory employed here has been outlined elsewhere\(^{13,15}\) so we will emphasize only the key points. A two-dimensional model potential between the incoming particles and the surface is assumed and written as

\[
U(x, z) = V(z) \cdot h(x)
\]

where \( V(z) \) describes the interaction along the coordinate \( z \) perpendicular to the surface and \( h(x) \) is the periodic surface along the horizontal coordinate \( x \). For the \( z \)-direction, the combination of a Morse potential, \( V_M(z) \), at short distances, and an attractive van der Waals-Casimir tail \( V_C \), at large distances, has been shown to be a good description of this interaction

\[
V(z) = \begin{cases} 
V_M(z) = D \left[ e^{-2\chi z} - 2e^{-\chi z} \right], & z < \bar{z} \\
V_C(z) = -\frac{C_4}{(l+z)^2}, & z \geq \bar{z}
\end{cases}
\]
Here $C_4 = C_3 l$, $C_3$ being the van der Waals coefficient and $l$ a characteristic length which determines the transition from the van der Waals ($z \ll l$) to the Casimir ($z \gg l$) regime. The matching point $\bar{z}$ is usually determined by imposing both the continuity condition for the interaction potential and its first derivative. The range of variation of the $C_3$ parameter is usually known and the stiffness parameter of the Morse potential $\chi$ is considered a fitting parameter; $D$ is determined from the matching point $\bar{z}$.

The periodic grating function $h(x)$ is described by the so-called unit impulse function and written as

$$h(x) = \sum_{n=-\infty}^{+\infty} \prod \left( \frac{x-nd}{a} \right)$$

where $a$ is the width of the strips and $d$ the period with $a < d$. The $\prod(y)$-function is the so-called unit impulse function: $0$ for $|y| > 1/2$, $1$ for $|y| < 1/2$ and $1/2$ for $|y| = 1/2$. In terms of a Fourier series, $h(x)$ is expanded as

$$h(x) = \sum_{n=-\infty}^{+\infty} c_n e^{i2\pi nx/d}$$

with $c_0 = a/d$, $c_{-n} = c_n$ and $c_n = (a/d)\text{sinc}(na/d)$, and $\text{sinc}(x) = \sin(\pi x)/\pi x$. When $d = 2a$ (as in the experimental grating of Ref. [5]), the terms beyond the sixth order are quite small. The periodic interaction potential can then be expressed as

$$U(x, z) = \sum_{n=-\infty}^{+\infty} V_n(z)e^{i2\pi nx}$$

where the first term ($n = 0$) is the interaction potential $V_0(z) = V(z)$ (see Eq. [4]) and the coupling terms ($n \neq 0$) are given by

$$V_n(z) = 2\text{sinc}(\frac{a}{d})V(z)$$

where $d$ and $a$ are the period and width of the strips.

As has been recently shown [13,15], the elastic scattering of the incident particles with the surface is theoretically well described by the CC formalism. The corresponding CC differential equations are written as

$$\left[ \frac{\hbar^2}{2m} \frac{d^2}{dz^2} + \frac{\hbar^2}{2m} k_{n,z}^2 - V_0(z) \right] \psi_n(z) = \sum_{n\neq n'} V_{n-n'}(z)\psi_n'(z)$$

7
with $\hbar^2 k_{n,z}^2$ being the z-component of the kinetic energy of the scattered particles. The square z-component of the wave vector is given by

$$k_{n,z}^2 = k_i^2 - \left( k_i \sin \theta_i + \frac{2\pi n}{d} \right)^2. \quad (10)$$

with $\theta_i$ measured with respect to the normal to the surface. Thus, when comparing with experimental results, theoretical positive $n$ diffraction orders correspond to experimental negative ones. The effective potentials labelled by $n V_0(z) + \frac{\hbar^2}{2m} (k_i \sin \theta_i + 2\pi n/d)^2$ in Eq. (9) represent diffraction channels. The asymptotic energies depend on $n$ and the incident energy and polar angle. As is known, open (closed) diffraction channels have a positive (negative) normal kinetic energy $\hbar^2 k_{n,z}^2/(2m)$. The coupling between channels $V_{n-n'}(z)$ is given by Eq. (8) since $n - n'$ is always an integer number. The diffraction intensities or reflection probabilities, obtained by solving the CC equations given by Eq. (9) with the usual boundary conditions, are expressed as

$$I_n = |S_{n0}|^2 \quad (11)$$

where $S_{nn'}$ are the elements of the unitary scattering matrix. Their square absolute values give the diffraction intensity or probability for an incident wave at the specular channel ($n' = 0$) and exiting by any of the open diffraction channels labelled by $n$.

As mentioned above, the interaction potential given by Eq. (4) displays classical turning points due to the repulsive part of the Morse potential. To distinguish between quantum threshold reflection and classical reflection from the inner repulsive part of the Morse potential, absorbing boundary conditions have to be imposed in the inner part. A Woods-Saxon (WS) potential is added to the imaginary part of the diffraction channel potentials

$$V_{WS} = \frac{A}{1 + e^{\alpha \chi(z-z_i)}} \quad (12)$$

which is essentially zero in the physically relevant interaction region and turns on sufficiently rapidly but smoothly at the left edge of the numerical grid for the integration to absorb the flux. The fitting parameters of this WS potential are $A$ and $\alpha$. The resulting scattering matrix $\tilde{S}$ is then no longer unitary. The diffraction intensities are given by $\bar{I}_n = |\tilde{S}_{n0}|^2$ and the total quantum reflection probability is calculated as

$$P^{QR} = \sum_n |\tilde{S}_{n0}|^2 < 1 \quad (13)$$
TABLE I: Parameters of the interaction potential $V(z)$ for the four surfaces. The stiffness parameter of the Morse potential, $\chi$, is a free parameter fitted to reproduce the corresponding experimental results and $D$ is the well depth. The characteristic lengths $l$ and parameters $C_3$ are based on values reported in previous works.

<table>
<thead>
<tr>
<th>Parameters</th>
<th>Glass slide</th>
<th>GaAs wafer</th>
<th>Flat Cr</th>
<th>Structured Cr</th>
</tr>
</thead>
<tbody>
<tr>
<td>$\chi , (\text{Å}^{-1})$</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
</tr>
<tr>
<td>$D , ($meV)</td>
<td>9.8</td>
<td>15.3</td>
<td>9.8</td>
<td>9.8</td>
</tr>
<tr>
<td>$l , (\text{Å})$</td>
<td>93</td>
<td>93</td>
<td>93</td>
<td>93</td>
</tr>
<tr>
<td>$C_3 , (10^{-50} , \text{J m}^3)$</td>
<td>3.5</td>
<td>5.5</td>
<td>3.5</td>
<td>3.5</td>
</tr>
</tbody>
</table>

for each initial condition. Due to the absorbing potential the theoretical diffraction efficiencies are defined as the ratio of the diffraction intensity $\bar{I}_n$ to the total quantum reflection probability $P_{QR}$ rather than to the total incident flux in order to compare to the experimental results.

For flat surfaces $h(x) = 1$ and no diffraction channels are present, only specular reflection is present. The WS potential is then added to the specular channel.

IV. RESULTS AND DISCUSSION

The parameters used in the elastic CC calculations for the perpendicular potential are displayed in Table I. As previously noted, the only real fitting parameter is $\chi$ since the values of $C_3$ have been taken from Ref. and only slightly modified. The values obtained from fitting to the experimental results when solving numerically the one-dimensional Schrödinger equation only for the attractive potential were $3, 5, 3$ and $3 \times 10^{-50} \, Jm^3$ for the glass slide, wafer, flat and structured Cr, respectively. The well depth is related to $\chi$ according to our procedure to evaluate the matching point $\bar{z}$. A characteristic length $l$ of 9.3 nm for He for the transition from the Casimir to the van der Waals regimes in the long range attractive potential is a well accepted value in the literature. For the numerical integration, the range of distances was taken to be -13 to 2,000 Å.
Reflection probabilities for He atoms scattering from a glass slide at three different source temperatures 8.7 K (black labels), 50 K (red labels) and 300 K (blue labels). In the top panel, probabilities are plotted as a function of $k_{\text{perp}}$ in nm$^{-1}$ whereas in the bottom panel, they are plotted versus the incident angle in mrad. Points are the experimental results and crosses the results of the present elastic CC computations.

The parameters of the WS potential were varied with the incident wave vector. The detailed procedure for using these complex absorbing boundary conditions for the diffraction channels has been described elsewhere.$^{13,15}$ Due to the fact that no information is available on the structure of the experimental surfaces used, we have assumed that they are flat, except for the structured Cr surface. Thus, $h(x) = 1$ is chosen for the glass slide, GaAs wafer and flat Cr surfaces leading to only specular reflection or reflectivity. The characteristics of the grating Cr surface are the same as reported in Ref.$^5$ with $h(x)$ given by Eq. (6).

Reflection probabilities for He atoms scattering from a glass slide at three different source temperatures of 8.7 K (black labels), 50 K (red labels) and 300 K (blue labels) are plotted in Figure 1 as a function of $k_{\text{perp}}$ in nm$^{-1}$ (top panel) and versus the incident angle in mrad (bottom panel). Points are the experimental results and crosses our elastic CC results. The overall agreement is fairly good. The universal linear behavior of the quantum reflection probability in the top panel is observed for $k_{\text{perp}}$ values between 0.2- 0.3 nm$^{-1}$, depending
on the stagnation temperature. After this small region of $k_{\text{perp}}$, one finds that the value of $k_{\text{perp}}$ causes this probability to fan out. The same is observed in the bottom panel where the incident angle also contributes to this effect. The quantum threshold reflection clearly decreases with $k$ and $\theta_i$.

Whereas the same observations are extracted from analyzing the experimental and theoretical results, our interpretation is different. We attribute our results to only quantum threshold reflection, not to classical reflection from the inner region of the potential even at higher $k_{\text{perp}}$. Our theoretical calculations are preventing classical reflection due to the use of the complex absorbing boundary conditions. The classical turning points of the perpendicular potential are not reached. The universal linear behavior is gradually lost with increasing $k_{\text{perp}}$ because the next quadratic term is contributing in the expansion of the exponential function mentioned in the Introduction. The transition from quantum to classical reflection cannot be observed by varying the incident wave vector. Moreover, from our calculations, it becomes clear that the fanning out effect observed for this surface should not be attributed to the surface roughness as mentioned in Ref.\textsuperscript{6} since we used a flat surface.

The same arguments and conclusions are valid also for the GasAs wafer surface whose results are plotted in Figure\textsuperscript{2}. The degree of this fanning out is the smallest for the wafer as compared to the three other surfaces studied. The hierarchy of surface roughness determined by qualitative AFM measurement\textsuperscript{6} indicates that the root-mean-square surface roughness is smallest for the chromium surface. In particular, the glass slide is larger than for the wafer. It is thus suggestive that the extent of surface roughness affects the extent of fanning out at higher $k_{\text{perp}}$. However, from our computations we conclude that this roughness has at most a minor effect on the quantum threshold reflection.

The next two surfaces are interesting to study to see what is the real effect of the roughness. In Figures\textsuperscript{3} and \textsuperscript{4} we present the quantum reflection probabilities for a flat and structured chromium surface, respectively. The linear behavior seems to take place for perpendicular wave vectors less than 0.2 nm$^{-1}$ in both cases. The fanning out effect is also more pronounced in the structured surface. However, the conclusions are the same as previously mentioned for the other two surfaces.
V. CONCLUDING REMARKS

In this work, we presented a theoretical study, based on the closed coupled equations method, of the scattering of He atom beams at grazing angles and threshold conditions
on four surfaces; a glass slide, a GaAs wafer, and a flat and structured chromium surface. The reasonable agreement between our results and the experimental ones indicates the reflection observed in the experiment should be attributed solely to quantum threshold reflection and not to classical reflection from the repulsive inner region of the potential. For all the surfaces studied we also observe the fanning out effect of the reflection probability with increasing incident energy but attribute this to the quantum threshold reflection rather than the classical reflection from the inner turning point. The universal linear dependence of the reflection probability on the perpendicular component of the incident wave vector gradually turns into a quadratic term, as might be expected from the next order in the expansion of the dependence of the reflection coefficient on the incident wave-vector: $|R| \sim \exp(-2k_{\text{perp}}b) \sim 1 - 2k_{\text{perp}}b + 2k_{\text{perp}}^2b^2$. Finally, the decrease of the quantum threshold reflection probability with the incident wave vector and incident angle is found to be less pronounced for the wafer and much more for the structured Cr surface due to its roughness. The present computational result again indicates that the whole interaction potential is needed to correctly describe the quantum threshold reflection phenomenon, not only qualitatively but also quantitatively.
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